

YJ Planar Schottky Barrier Diode Die Specification

30V 0.2A,13mil, Schottky barrier diode die based on silicon planar process
Part No.: PSB013L030AG-155E

Main Products Characteristics

- Average forward current: IF(AV) = 0.2 A
- Maximum operating junction temperature: Tj = 125 °C
- ESD rating: >2KV, per IEC61000-4-2 (Contact Discharge)
- Top metal: AL/3.915um

Maximum Ratings

Static Electrical Characteristics (Ta = 25°C)

IF =200mA
Pulse Test: tp = 800 μs, δ ≤ 2%

Device Schematics and Outline Drawing

- Die Thickness *
- Die Size **
- Top Metal Pad
- Active Area
- Top Metal
- Back Metal
- Steet width

Important Notice

Specification apply to die only. Actual performance may degrade when assembled.

Recommended Storage Environment:

does not guarantee device performance after assembly.

Store in original container, in dessicated nitrogen, with no contamination.

All operating parameters must be valida14(i)14(d)9(a)9(14)da 4(d)9(a)a **(R)**(i)14(t)-4[R) muarater apificatiomaRmuarates